/ Descriptions

VRS0; ṂṂ Ł Q ڜ Sr z hu Wuhq f k P RV ᵡ ʃ ᾧ Ẓ ٦

Dual N-Channel Power Trench MOSFET in a SOP-8 Plastic Package.

/ Features

V_{DS}(V)=40V I_D=8A

$R_{DS(ON)}$@10V<20mΩ(Typ. 22mΩ)

$R_{DS(ON)}$)@4.5V<29.5mΩ(Typ. 36mΩ)

ṇ ꜰ β HF Product.

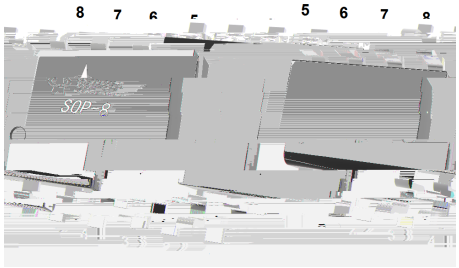
/ Applications

ɔ – Ȝ ǐ ı ق ڒ Ầ ʜ ı ɔ ◊ ٦ ת

Battery protection, Load Switch, Power management.

/ Equivalent Circuit

/ Pinning



PIN1 χ S1 PIN 2 χ G1 PIN 3 χ S2 PIN 4 χ G2

PIN 5 χ D2 PIN 6 χ D2 PIN 7 χ D1 PIN 8 χ D1

/ Marking

ð м ٦ ب ˝

See Marking Instructions.

/ Electrical Characteristics(Ta=25)

v ̈Ω Parameter	ϒ N Symbol	╨ ;ˆ Ţ Test Conditions	ѡ ṇ Ө Min	Ɛ ʒ Ө Typ	ѡ ᶻ Ө Max	D Ꮋ Unit
Total Gate Charge	Q_g(10V)	V_{GS}=10V V_{DS}=20V I_D=6A		15.4		nC
Total Gate Charge	Q_g(4.5V)			7.0		
Gate-Source Charge	Q_{gs}			1.4		
Gate-Drain Charge	Q_{gd}			2.9		

/ Electrical Characteristic Curve

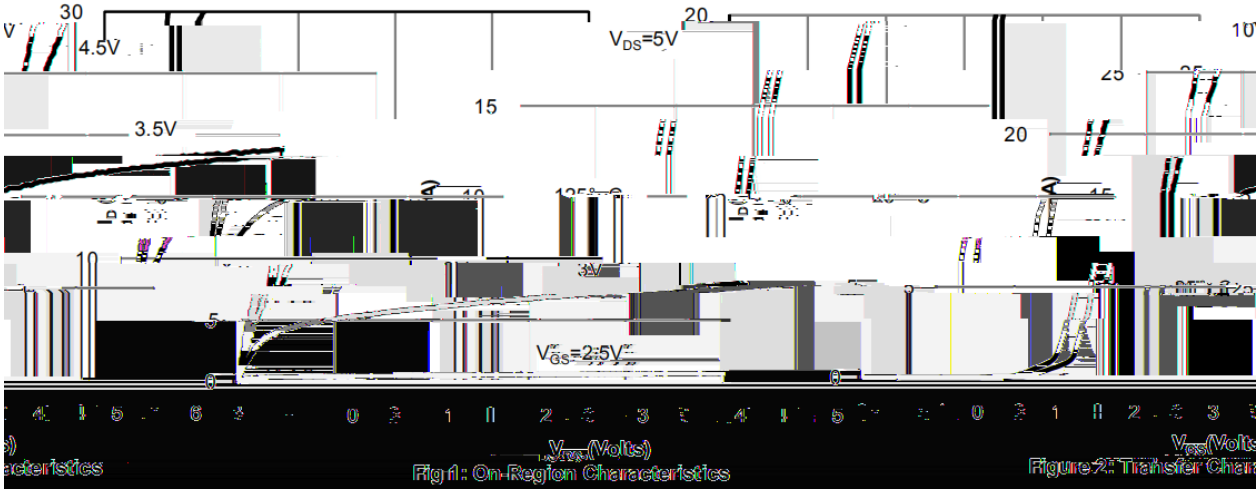


Fig 1: On-Region Characteristics

Figure 2: Transfer Char

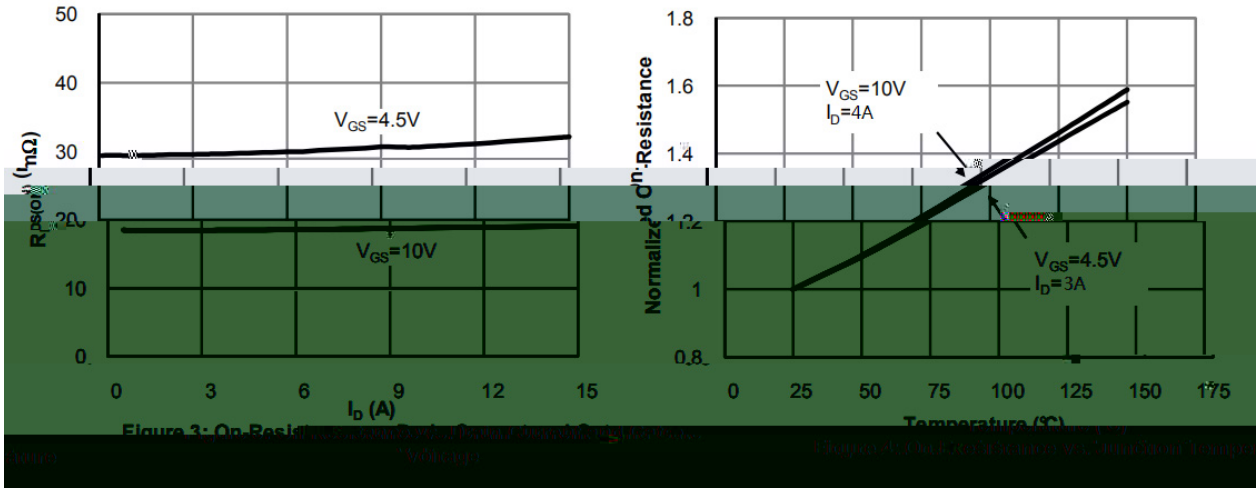
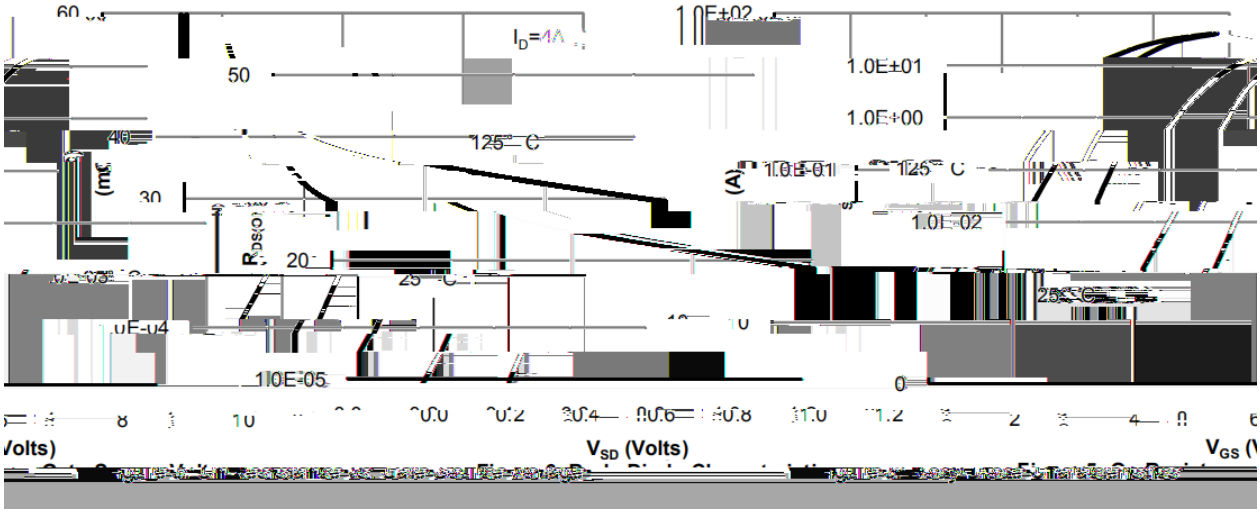
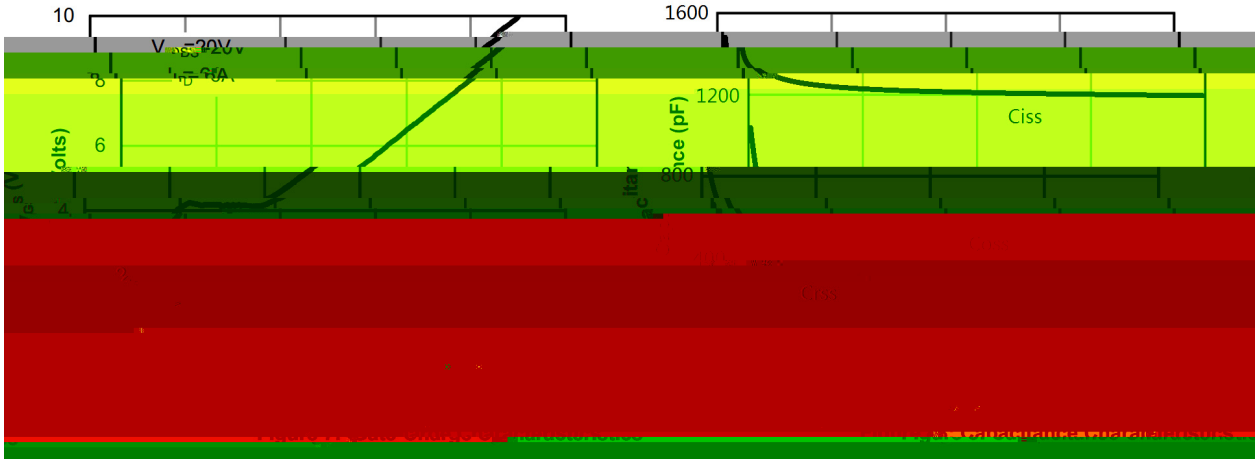
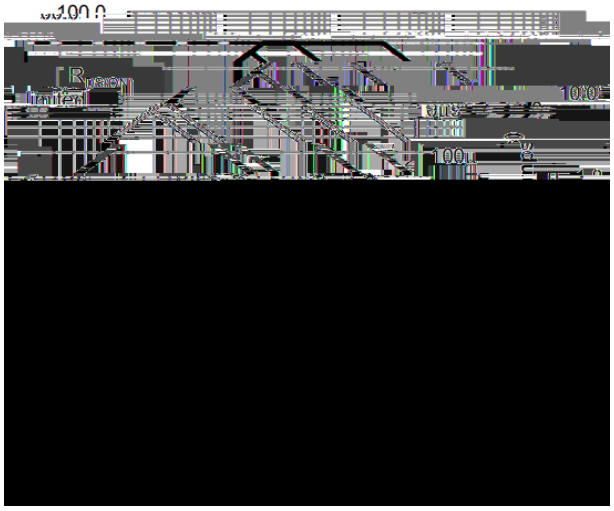


Figure 3: On-Resi



/ Electrical Characteristic Curve





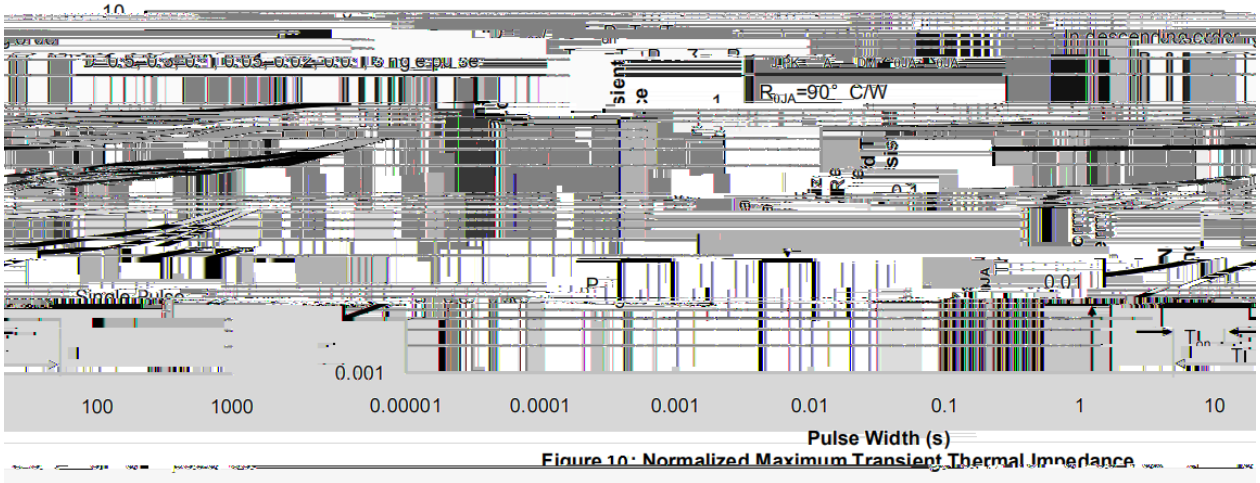


Figure 10: Normalized Maximum Transient Thermal Impedance

/ Package Dimensions

, M y ƒ / Marking Instructions

BR
200N04D

ª ¢ y

BR y ¸ [W A

4 * y º Z W A

y ÿ D Z W A k š ÿ D Z J

Note:

BR:	Company Code.
200N04D y	Product Type.
****:	Lot No. Code, code change with Lot No

š WD t … • Ž ¢ (x /) / : K S V K X G Z [X K 6 X U L O R K L U X / 8 8 K L R U] 9 U R J K X O T M 6

ª ¢ y

1o• Ä ½ “ † 150 ½180 - k ž • 60 ½90sec;

2o• Q › “ † 245 r 5 - k ž • 4 Ò 5 r 0.5sec;

3o•D N ò i Ò 0 , † 2 ½10 - /sec.

Note:

1.Preheating:150~180 - , Time:60~90sec.

2.Peak Temp.:245 r 5 - , Duration:5 r 0.5sec.

3.